

B. Claims

The following is a complete listing of the claims, and replaces all earlier versions and listings.

1. (Previously Presented) A processing apparatus that provides a plasma treatment to an object, said processing apparatus comprising:
 - a process chamber that accommodates an object to be processed and generates plasma;
 - a gas introducing part for introducing gas into the process chamber;
 - a mechanism that arranges the object in a flow of the gas such that the object is (i) closer to the gas introducing part than to a plasma generating region and (ii) between the gas introducing part and the plasma generating region in the flow of the gas;
 - and
 - an exhaust mechanism, which is arranged closer to the plasma generating region than to the object, for exhausting the gas.
2. (Original) A processing apparatus according to claim 1, further comprising, between the object and the plasma generating region, a conductance adjuster for maintaining, within a predetermined range, a concentration of active species in a process space that encloses the object.
3. (Original) A processing apparatus according to claim 2, wherein said conductance adjuster is a plate bored with plural holes.

4. (Original) A processing apparatus according to claim 2, further comprising an exhaust mechanism at a side of the plasma generating region in that is partitioned by said conductance adjuster, wherein said gas introducing part is located at a side of the object in said process chamber that is partitioned by said conductance adjuster.

5. (Original) A processing apparatus according to claim 2, wherein said gas introducing part includes a first gas inlet for introducing into said process chamber process gas for the plasma treatment to the object, and a second gas inlet for introducing inert gas into said process chamber, and

wherein said processing apparatus further comprises an exhaust mechanism at a side of the plasma generating region in said process chamber that is partitioned by said conductance adjuster, and

wherein the first gas inlet is located at the side of the plasma generating region in said process chamber that is partitioned by said conductance adjuster, and the second gas inlet is located at a side of the object side in said process chamber that is partitioned divided by said conductance adjuster.

6. (Original) A processing apparatus according to claim 1, wherein the plasma treatment is oxidation or nitridation to a surface of the object.

7-20. (Cancelled).